Mark Lundstrom

List of Publications by Year
in descending order

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24	7,792	471061 17	676716 22
papers	citations	h-index	g-index

25	25	25	6493
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Signatures of Disorder in the Minimum Conductivity of Graphene. Nano Letters, 2011, 11, 1319-1322.	4.5	27
2	Ultimate device scaling: Intrinsic performance comparisons of carbon-based, InGaAs, and Si field-effect transistors for 5 nm gate length. , 2011, , .		65
3	Investigative Tools: Theory, Modeling, and Simulation. , 2011, , 29-69.		4
4	Device Simulation of SWNT-FETs. Integrated Circuits and Systems, 2009, , 107-131.	0.2	14
5	CARBON NANOTUBE FIELD-EFFECT TRANSISTORS. Selected Topics in Electornics and Systems, 2007, , 15-30.	0.2	1
6	Performance Analysis of a Ge/Si Core/Shell Nanowire Field-Effect Transistor. Nano Letters, 2007, 7, 642-646.	4.5	157
7	CARBON NANOTUBE FIELD-EFFECT TRANSISTORS. International Journal of High Speed Electronics and Systems, 2006, 16, 897-912.	0.3	32
8	Role of phonon scattering in carbon nanotube field-effect transistors. Applied Physics Letters, 2005, 86, 193103.	1.5	93
9	Performance evaluation of ballistic silicon nanowire transistors with atomic-basis dispersion relations. Applied Physics Letters, 2005, 86, 093113.	1.5	47
10	Theoretical investigation of surface roughness scattering in silicon nanowire transistors. Applied Physics Letters, 2005, 87, 043101.	1.5	134
11	High-Field Quasiballistic Transport in Short Carbon Nanotubes. Physical Review Letters, 2004, 92, 106804.	2.9	543
12	3D Electrostatics of Carbon Nanotube Field-Effect Transistors. Journal of Computational Electronics, 2004, 3, 277-280.	1.3	4
13	Atomistic Simulation of Carbon Nanotube Field-Effect Transistors Using Non-Equilibrium Greenâ€™s Function Formalism. Journal of Computational Electronics, 2004, 3, 373-377.	1.3	24
14	A Quantum Mechanical Approach for the Simulation of Si/SiO2 Interface Roughness Scattering in Silicon Nanowire Transistors. Journal of Computational Electronics, 2004, 3, 453-457.	1.3	4
15	Self-Aligned Ballistic Molecular Transistors and Electrically Parallel Nanotube Arrays. Nano Letters, 2004, 4, 1319-1322.	4.5	505
16	A three-dimensional quantum simulation of silicon nanowire transistors with the effective-mass approximation. Journal of Applied Physics, 2004, 96, 2192-2203.	1.1	328
17	Carbon Nanotube Field-Effect Transistors with Integrated Ohmic Contacts and High-Î¹ Gate Dielectrics. Nano Letters, 2004, 4, 447-450.	4.5	498
18	Toward Multiscale Modeling of Carbon Nanotube Transistors. International Journal for Multiscale Computational Engineering, 2004, 2, 257-276.	0.8	224

#	Article	IF	Citations
19	Ballistic carbon nanotube field-effect transistors. Nature, 2003, 424, 654-657.	13.7	2,883
20	Metalâ€“insulatorâ€“semiconductor electrostatics of carbon nanotubes. Applied Physics Letters, 2002, 81, 1486-1488.	1.5	114
21	Performance projections for ballistic carbon nanotube field-effect transistors. Applied Physics Letters, 2002, 80, 3192-3194.	1.5	200
22	High-Îº dielectrics for advanced carbon-nanotube transistors and logic gates. Nature Materials, 2002, 1, 241-246.	13.3	928
23	Minority electron transport in InP/InGaAs heterojunction bipolar transistors. Applied Physics Letters, 1992, 61, 465-467.	1.5	32
24	Consequences of valley filtering on abrupt junction AlGaAs/GaAs heterojunction bipolar transistors. Journal of Applied Physics, 1989, 66, 2168-2172.	1.1	6